Appl. No. 10/707,244
Amdt. dated May 22, 2006
Reply to Office action of March 03, 2006

## Listing of Claims:

1. (original): An optical proximity correction (OPC) method for correcting a photomask layout, wherein the photomask layout comprises at least a photomask pattern, the OPC method comprising:

   collecting an assist feature bias of a predetermined first assist feature which will be added to the photomask layout;

   performing a rule-based OPC process by taking account of the assist feature bias to compute a target bias of the photomask layout and output a corrected photomask layout according to the target bias; and

   adding the first assist feature to the corrected photomask layout.

2. (original): The OPC method of claim 1, wherein the first assist feature is a scattering bar.

3. (original): The OPC method of claim 1, further comprising using the collected assist feature bias to build an assist feature correction model for the rule-based OPC process.

4. (original): The OPC method of claim 1, further comprising transferring the collected assist feature bias to a specific format for the ruled-based OPC process.

5. (original): The OPC method of claim 1, wherein the rule-based OPC process is used for correcting an edge portion of the photomask pattern.

6. (original): The OPC method of claim 1, wherein the rule-based OPC process comprises:

   collecting a width and a spacing of the photomask pattern to obtain a parameter of the

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photomask pattern; and

adding a second assist feature using a correction rule of a database according to the

parameter of the photomask pattern.

5    7.    (original): The OPC method of claim 6, wherein the second assist feature is a serif or

a hammerhead pattern.


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